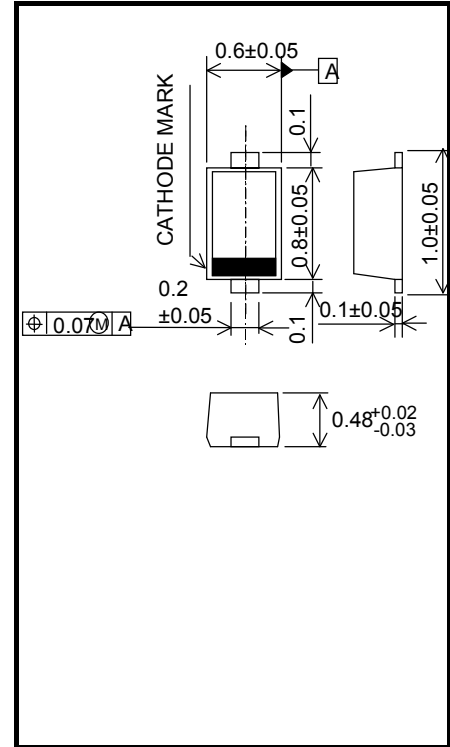


Diodes for Protecting against ESD Epitaxial Planar Type

HBZD12FS

Product for Use Only as Protection against Electrostatic Discharge (ESD).

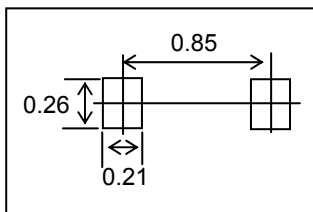
Unit: mm



Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Power dissipation	P*	150	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55~150	°C

Pad Dimension(Reference) Unit: mm



Electrical Characteristics (Ta = 25°C)

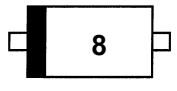
Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Zener voltage	V _Z	—	I _Z = 5 mA	11.4	12.0	12.6	V
Dynamic impedance	Z _Z	—	I _Z = 5 mA	—	—	25	Ω
Reverse current	I _R	—	V _R = 9 V	—	—	0.05	μA
Total capacitance	C _T	—	V _R = 0 V, f = 1 MHz	—	15	—	pF

Guaranteed Level of ESD Immunity

Test Condition	ESD Immunity Level
IEC61000-4-2 (Contact discharge)	± 30 kV

Criterion: No damage to device elements

Marking



Equivalent Circuit (Top View)

